



# UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE  
United States Patent and Trademark Office  
Address: COMMISSIONER FOR PATENTS  
P.O. Box 1450  
Alexandria, Virginia 22313-1450  
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/539,875	03/24/2006	Corinne Perret	9905/29	6339

7590 04/10/2009  
Brinks Hofer Gilson & Lione  
PO Box 10395  
Chicago, IL 60610

EXAMINER
----------

ANGADI, MAKI A

ART UNIT	PAPER NUMBER
----------	--------------

1792

MAIL DATE	DELIVERY MODE
-----------	---------------

04/10/2009

PAPER

**Please find below and/or attached an Office communication concerning this application or proceeding.**

The time period for reply, if any, is set in the attached communication.

<b>Office Action Summary</b>	<b>Application No.</b> 10/539,875	<b>Applicant(s)</b> PERRET ET AL.	
	<b>Examiner</b> MAKI A. ANGADI	<b>Art Unit</b> 1792	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

### Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

### Status

- 1) ☒ Responsive to communication(s) filed on 3/10/2009.
- 2a) ☒ This action is **FINAL**.                      2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

### Disposition of Claims

- 4) ☒ Claim(s) 1-11 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-11 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

### Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

### Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All    b) ☐ Some \*    c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
  2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
  3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

### Attachment(s)

- |  |   |
|--|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)          | 4) <input type="checkbox"/> Interview Summary (PTO-413)           |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | Paper No(s)/Mail Date. _____                                      |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO/SB/08)          | 5) <input type="checkbox"/> Notice of Informal Patent Application |
| Paper No(s)/Mail Date _____  | 6) <input type="checkbox"/> Other: _____                          |

## **DETAILED ACTION**

### ***Response to Amendment***

1. Examiner acknowledges amendments to claim 1 filed on 3/10/2009 and the amendments are entered.

### ***Claim Rejections - 35 USC § 103***

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

2. Claims 1-5 and 8-9 are rejected under 35 U.S.C. 103(a) over Chou (US Patent No. 5, 772,905) in view of Sun et al. Journal of Vacuum Science & Technology, B 16(6), Nov./Dec (1998) pages 3922-3925.

Art Unit: 1792

*As to claim 1*, Chou discloses a lithography method (col.2, lines 19-21) that reads on the process of pressing of a substrate (18) (Fig.1A) wherein the substrate is covered with a layer (20) (col.4, lines 10-12) a pressing step in which a mold (10) comprising a pattern of recesses and protrusions (16) (Fig.1A) is pressed so as to penetrate part of the thickness of the layer (20) (Fig.1B) (col.4, lines 13-19), etching using etching pattern defined by the mold pattern (Fig.1C)(col.4, lines 26-37), a step involving a curable material such as PMMA (20) spun on a silicon wafer (18) (col.4, lines 57-67), the pressing step including penetration of the protrusions of the mold(14) into the external sub-layer (20) until it comes into contact with protrusions contact the internal sub-layer ((20) (Fig.1C-D).

Chou does not expressly disclose the etching step in which the layer is attacked until part of the surface of the substrate have been exposed. One who is skilled in the art would expect the stripping or removal of the layer in the process of etching by either reactive ion etching or wet etching employed by Chou (col.4, lines 33-35).

Chou does not expressly disclose the formation of a composite layer in the lithographic process.

However, Sun discloses a composite trilayer (Fig.1A) consisting of a planarization (bottom) layer, middle layer and the top layer (col.1, page 3922, paragraph 3) in the nanoimprint lithography.

Therefore, one who is skilled in the art at the time of the invention was made to select the composite layer because Sun illustrates in Fig.1A that the composite trilayer is useful for nano-imprint lithography on non-flat surfaces and has the potential for low-cost and high throughput for 10 nm feature size (col.1, paragraph 1, and page 3922).

*As to claim 2*, Chou discloses steps that read on the internal sub-level (20) being formed in contact with the surface substrate (18) during attacking/etching step, the internal sub-layer is removed through the recesses of the external sub-layer (14), during the substrate etching step, the substrate is etched through the same recesses (Fig.1B, col.4, lines 13-26).

*As to claim 3*, Chou discloses the method of forming the internal sub-layer (20) made of a thermoplastic polymer (col.4, lines 50-51) and the external sub-layer is made of softened thin film (col.4, line 45). Chou does not expressly disclose that the internal sub-layer and the external sub-layer is the same material. One who is skilled in the art should be able to select same material for both sub-layers that are soft using compressing molding of thermoplastic polymers suitable for nanoimprint lithography (col.1, lines 61-63).

*As to claim 4*, Chou discloses a method that includes the heating (curing) at a temperature higher than the curing temperature and the pressing step at a

Art Unit: 1792

pressing temperature higher than the glass transition temperature of the external sub-layer (col.4, lines 65-67, col.5, lines 1-8).

*As to claim 5*, Chou discloses that the curable material is a polymer (PMMA, polymethyl methacrylate) (col.4, lines 57-58).

*As to claim 8*, Chou discloses a method so that the internal sub-layer (20) (Fig.1A) has a thickness of about 50 nm to about 250 nm, which is slightly higher than the thickness claimed by the applicant. One who is skilled in the art at the time the invention should be able to adjust the film thickness to optimize conditions for lithography (col.3, lines 52-67).

*As to claim 9*, Chou discloses a method wherein forming external sub-layer (50-250 nm) (col.4, lines 57-59) to a thickness less than the depth of the pattern of recesses depending on the desired lateral dimension (col.4, lines 43-45). One who is skilled in the art at the time the invention was made to select these dimensions to optimize the conditions for lithography of sub-25 nm resolution (col.3, lines 52-67).

***Claim Rejections - 35 USC § 103***

3. Claims 6 is rejected under 35 U.S.C. 103(a) over Chou (US Patent No. 5, 772,905) in view of Sun et al. Journal of Vacuum Science & Technology, B 16(6),

Nov./Dec (1998) pages 3922-3925 as applied to claim 1 above, in further view of Pavlinec *Journal of Polymer Science, Vol.55, (1995) pages 39-45*.

Chou does not expressly disclose that the polymer can be cross-linked. However, Pavlinec discloses that PMMA polymer can be cross-linked by chemical reactions (col.1, page 41, and paragraph 3). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to select polymer such as PMMA which can be cross-linked because Pavlinec illustrates that PMMA can be cross-linked by chemical reactions of linear macromolecules with multifunctional compounds (page 41).

***Claim Rejections - 35 USC § 103***

4. Claims 7 and 10 are rejected under 35 U.S.C. 103(a) over Chou (US Patent No. 5, 772,905) in view of Sun et al. *Journal of Vacuum Science & Technology, B* 16(6), Nov./Dec (1998) pages 3922-3925 and Pavlinec *Journal of Polymer Science, Vol.55, (1995) pages 39-45* as applied to claim 1 and 6, in further view of Allen, *IBM Journal of Research and Technology, Vol.41, No.1/2, (1997) pages 95-102*.

Chou discloses the use of a PMMA forming a resist pattern (col.3, lines 34-37) but does not expressly disclose being a positive or a negative resist. However, Allen discloses that PMMA forms a positive resist pattern in lithography (page 98). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to select PMMA in the lithography because

Allen illustrates that PMMA forms a 193 nm resist pattern because of their excellent optical transparency (page 1997).

***Claim Rejections - 35 USC § 103***

5. Claim 11 is rejected under 35 U.S.C. 103(a) over in view of Sun et al. Journal of Vacuum Science & Technology, B 16(6), Nov./Dec (1998) pages 3922-3925 in view of Chou (US Pub.No. 2002/0042027)).

Sun discloses a lithographic method which reads on the process (page 3922, col.1, paragraph 1) comprising: forming a first layer (planarization layer) (Fig.1B) (page 3923) on a substrate, the first layer comprising a curable material, and curing the first layer (col.2, paragraph 3, page 3922, lines 1-5), forming a second layer (PMMA) on the on the first layer, Pressing a mold against the second layer (Fig.1B), wherein protrusion of the mold form recesses in the second layer that expose portion of the first layer (Fig. 1B); etching the exposed portions of the first layer using the second layer as an etch mask, and exposing surface regions of the substrate (col.2, paragraph 3922, paragraph 3); and etching the surface regions of the substrate (col.2, paragraph 3 line 16).

Sun discloses the use of second layer PMMA (polymethyl methacrylate) on the first layer but does not expressly disclose that PMMA is a deformable material. However, Chou discloses the use of a deformable material such as a PMMA (paragraph 0035, Fig.1) in the microscale patterning for nanoimprint lithography (paragraphs 0033-0034). Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention was made to select a

deformable material in the microscale patterning because Chou illustrate in Fig.1 that the use of PMMA as a deformable material provides accurate control of the lateral location and orientation of a self-assembled structure (paragraph 0012).

### ***Response to Arguments***

6. Applicant's arguments with respect to claims 1-5 and 8-10 on pages 5-7 of the reply filed on 12/22/2008 have been considered but are moot in view of the new ground(s) of rejection.

A new prior art of Sun et al. (J.Vac.Sci & Technol, 1998) discloses the process of forming a composite layer, internal sub-layer of curable material. The combined prior art of Sun et al. and Chou meet the limitations of independent claims 1 and 11.

The reference of Sun teaches the step of removing an internal sub-layer, curing of the inner sub layer followed by etching regions of the substrate (see discussion on page 3).

### ***Conclusion***

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory

Art Unit: 1792

action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Tavkhelidze (US Patent No. 6, 680,214) discloses an artificial band gap.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Maki A. Angadi whose telephone number is 571-272-8213. The examiner can normally be reached on 8 AM to 4.30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine G. Norton can be reached on 571-272-1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR

Art Unit: 1792

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Maki A Angadi/  
Examiner, Art Unit 1792

/Shamim Ahmed/  
Primary Examiner, Art Unit 1792